

ASMMC.9CP1DV1D

PATENT

INFORMATION DISCLOSURE STATEMENT

Applicant	:	Arthur Sherman
App. No.	:	Unknown
Filed	:	Herewith
For	:	SEQUENTIAL CHEMICAL VAPOR DEPOSITION
Examiner	:	Unknown
Group Art Unit	:	Unknown

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing two hundred forty-three (243) references that were previously disclosed to or cited by the Patent and Trademark Office in the prosecution of U.S. patent application No. 09/866,156, filed May 24, 2001, which is the parent of this application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d). This Information Disclosure Statement is being filed with an RCE or within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: October 22, 2003

By: 

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMMC.9CP1DV1D	APPLICATION NO. To be assigned
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	4,058,430	11/15/77	Suntola et al.	156	611	11/25/75
	2.	4,282,267	08/04/81	Küyel			
	3.	4,389,973	06/28/83	Suntola et al.	118	725	12/11/81
	4.	4,747,367	05/31/88	Posa			
	5.	4,761,269	08/02/88	Conger et al.			
	6.	4,767,494	08/30/88	Kobayashi	156	606	09/19/86
	7.	4,845,049	07/04/89	Sunakawa	437	81	03/28/88
	8.	4,851,095	07/89	Scobey et al.			
	9.	4,859,627	08/22/89	Sunakawa	437	81	07/01/88
	10.	4,876,218	10/24/89	Pessa et al.	437	107	09/26/88
	11.	4,935,661	06/90	Heinecke et al.			
	12.	4,935,661-A	06/1990	Heinecke et al.			
	13.	4,993,357	02/19/91	Scholz	118	715	12/21/89
	14.	5,060,595	10/29/91	Ziv et al.	118	722	
	15.	5,071,670	12/10/91	Kelly	427	38	
	16.	5,130,269	07/14/92	Kitahara et al.	437	111	04/25/89
	17.	5,166,092	11/24/92	Mochizuki et al.	437	105	10/30/90
	18.	5,225,366	07/06/93	Yoder	437	108	07/22/90
	19.	5,256,244	10/26/93	Ackerman	156	613	02/10/92
	20.	5,270,247	12/14/93	Sakuma et al.	437	133	07/08/92
	21.	5,278,435	01/11/94	Van Hove			
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	23.	5,291,066	03/01/94	Neugebauer			
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	25.	5,300,186	04/05/94	Kitahara			
	26.	5,306,666	04/26/94	Izumi	437	192	07/21/93
	27.	5,321,713	06/14/94	Khan			

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U.S. PATENT DOCUMENTS							
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	31.	5,395,791	03/07/95	Cheng			
	32.	5,443,033	08/22/95	Nishizawa			
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	34.	5,458,084	10/17/95	Thorne			
	35.	5,469,806	11/28/95	Mochizuki			
	36.	5,483,919	01/16/96	Kitahara			
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	39.	5,618,395	04/08/97	Gartner			
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	41.	5,693,139	12/02/97	Nishizawa et al.	117	89	06/15/93
	42.	5,707,880	01/13/98	Aftergut			
	43.	5,711,811	01/27/98	Suntola			
	44.	5,730,802	03/24/98	Ishizumi			
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	49.	6,200,893	03/13/01	Sneh			
	50.	6,203,613	03/20/01	Gates et al.	117	104	10/19/99
	51.	6,270,572	08/07/01	Kim et al.	117	93	08/09/99
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FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	54.	WO 00/63957	26.10 00	PCT	H01L21	205		
	55.	0 442 490 A1	21.08 91	Europe				
	56.	0 526 779 A1	10.02 93	Europe				
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